

SAMTM Data Sheet SAM-1040-40-500fs-x, $\lambda = 1040$ nm

Laser wavelength $\lambda = 1040 \text{ nm}$

High reflection band (R > 55%) λ = 1010 .. 1100 nm

Absorbance $A_0 = 40 \ \%$ Modulation depth $\Delta R = 24 \ \%$ Non-saturable loss $A_{ns} = 16 \ \%$

Saturation fluence $\Phi_{\text{sat}} = 120 \,\mu\text{J/cm}^2$

Relaxation time constant $\tau \sim 500 \text{ fs}$ Damage threshold $\Phi = 1 \text{ mJ/cm}^2$

Chip area 4mm x 4mm; other dimensions on request

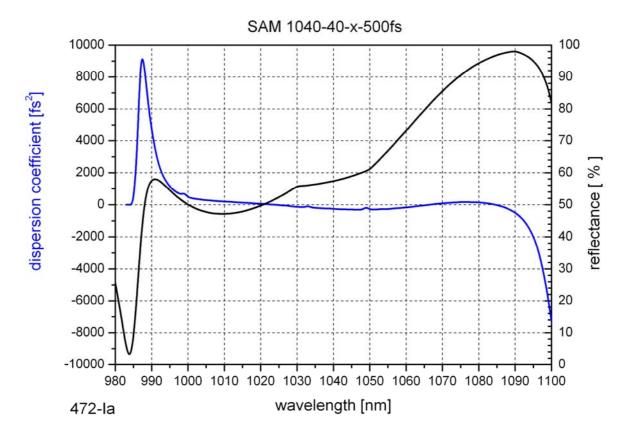
Chip thickness 400 µm; optional: 150 µm on request

Protection the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0
x = 12.7 g
x = 25.4 g
x = 12.7 s
x = 25.4 s
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Low intensity spectral reflectance and dispersion coefficient D₂





Group Delay Dispersion (GDD)

Dispersion coefficient
$$D_2(\omega)=\frac{\partial^2\varphi}{\partial\omega^2}$$
 with φ - reflected phase
$$\omega=2\pi\frac{c}{\lambda}$$
 - angular frequency

Low intensity spectral reflectance

